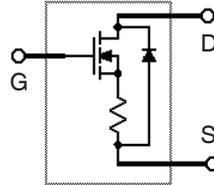


Gate Controlled Current Limiter

IXCY01N90E IXCP01N90E

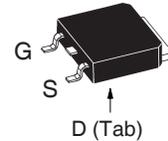
$V_{DSS} = 900V$
 $I_{D(limit)} = 250mA$
 $R_{DS(on)} \leq 80\Omega$

N-Channel Enhancement Mode

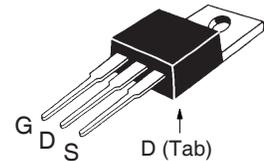


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	900	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	900	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
P_D	$T_C = 25^\circ C$	40	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062in.) from Case for 10s	300	$^\circ C$
T_{sold}	Plastic Body for 10 seconds	260	$^\circ C$
M_d	Mounting Torque (TO-220)	1.13 / 10	Nm/lb.in.
Weight	TO-220	3.00	g
	TO-252	0.35	g

TO-252 AA (IXCY)



TO-220 (IXCP)



G = Gate D = Drain
S = Source Tab = Drain

Features

- High Output Resistance in Saturated Mode of Operation
- Rugged HDMOS™ Process
- Stable Peak Drain Current Limit
- High Voltage Current Regulator
- International Standard Packages

Applications

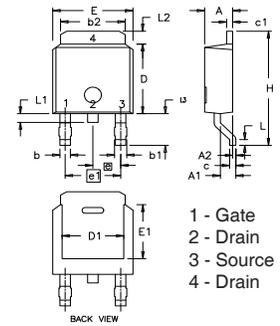
- Current Regulation
- Over Current and Over Voltage Protection for Sensitive Loads
- Linear Regulator

Symbol	Test Conditions ($T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 25\mu A$	900		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 25\mu A$	2.5		5.0 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 50 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$			10 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 50mA$, Note 1			80 Ω
I_{DP}	Plateau Current, $V_{GS} = 10V$, $V_{DS} = 10V$	125		175 mA

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}$, $I_D = 100\text{mA}$, Note 1		28	40 mS
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		158	pF
C_{oss}			22	pF
C_{rss}			6.6	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 50\text{V}$, $I_D = 50\text{mA}$ $R_G = 50\Omega$ (External)		21	ns
t_r			27	ns
$t_{d(off)}$			61	ns
t_f			74	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 50\text{mA}$		6.1	nC
Q_{gs}			0.9	nC
Q_{gd}			3.7	nC
$\Delta I_{A(p)}/\Delta T$	Plateau Current Shift with Temperature $V_{DS} = 10\text{V}$, $V_{GS} = 10\text{V}$		± 50	ppm/K
$\Delta V_{AK}/\Delta I_{A(p)}$	Dynamic Resistance, $V_{DS} = 20\text{V}$, $V_{GS} = 10\text{V}$	125		k Ω
V_F	$I_F = 50\text{mA}$, $V_{GS} = 0\text{V}$, Note 1			1.3 V
R_{thJC}				3.10 $^\circ\text{C}/\text{W}$
R_{thCS}		0.50		$^\circ\text{C}/\text{W}$
R_{thCA}	TO-220	80		$^\circ\text{C}/\text{W}$
	TO-252	125		$^\circ\text{C}/\text{W}$

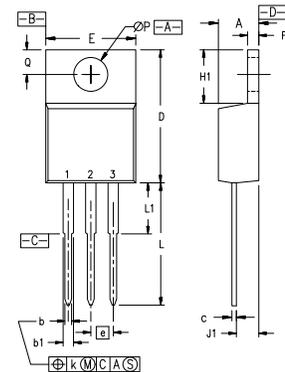
Note 1. Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

TO-252 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	2.19	2.38	0.086	0.094
A1	0.89	1.14	0.035	0.045
A2	0	0.13	0	0.005
b	0.64	0.89	0.025	0.035
b1	0.76	1.14	0.030	0.045
b2	5.21	5.46	0.205	0.215
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
D1	4.32	5.21	0.170	0.205
E	6.35	6.73	0.250	0.265
E1	4.32	5.21	0.170	0.205
e	2.28 BSC		0.090 BSC	
e1	4.57 BSC		0.180 BSC	
H	9.40	10.42	0.370	0.410
L	0.51	1.02	0.020	0.040
L1	0.64	1.02	0.025	0.040
L2	0.89	1.27	0.035	0.050
L3	2.54	2.92	0.100	0.115

TO-220 Outline



Pins: 1 - Gate 2 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics
@ $T_J = 25^\circ\text{C}$

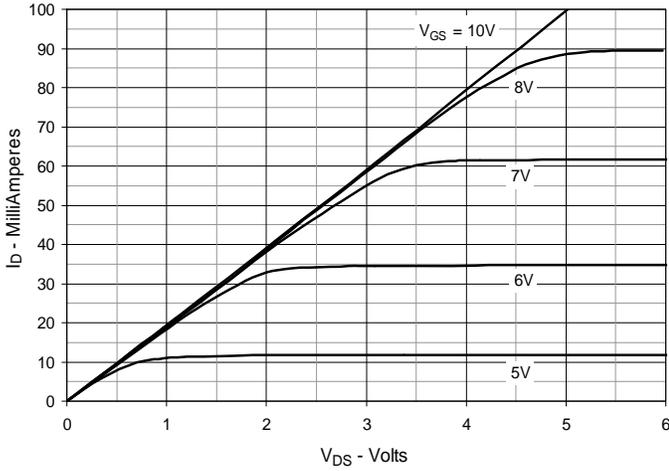


Fig. 2. Extended Output Characteristics
@ $T_J = 25^\circ\text{C}$

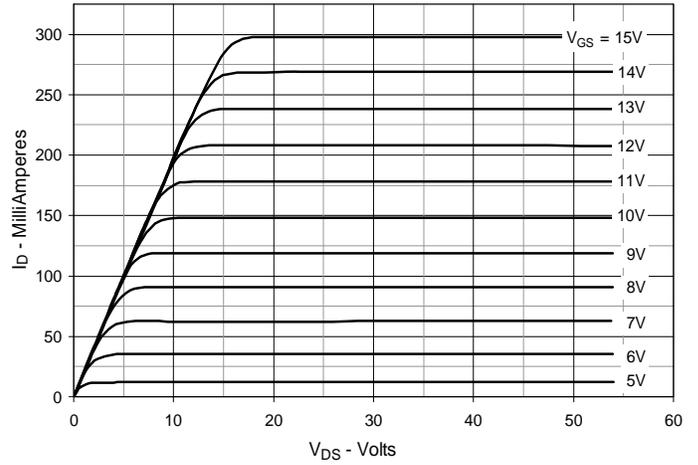


Fig. 3. Output Characteristics
@ $T_J = 125^\circ\text{C}$

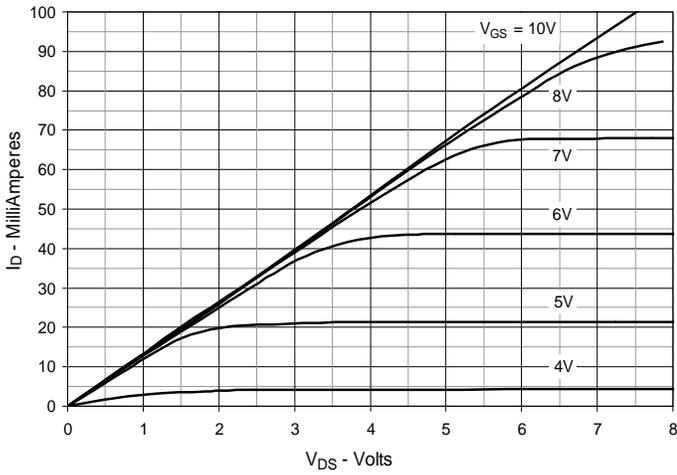


Fig. 4. Drain Current vs. Junction Temperature

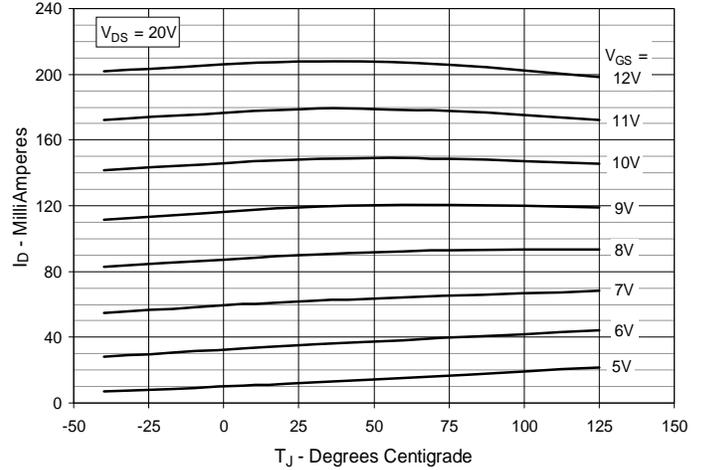


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 50\text{mA}$ Value vs. Junction Temperature

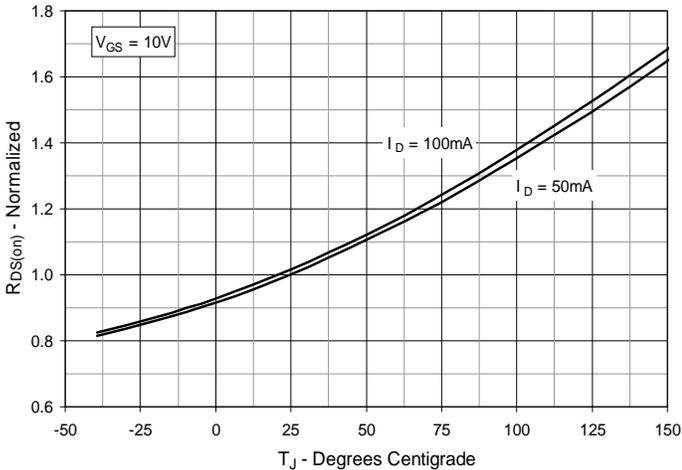


Fig. 6. $R_{DS(on)}$ Normalized to $I_D = 50\text{mA}$ Value vs. Drain Current

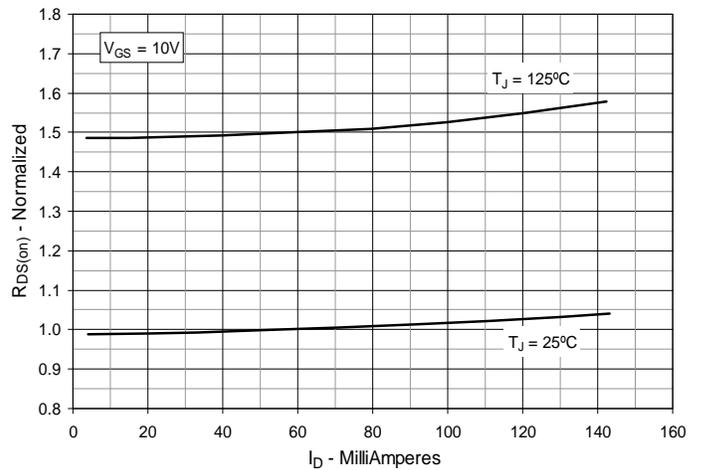


Fig. 7. Dynamic Output Resistance vs. Drain Current

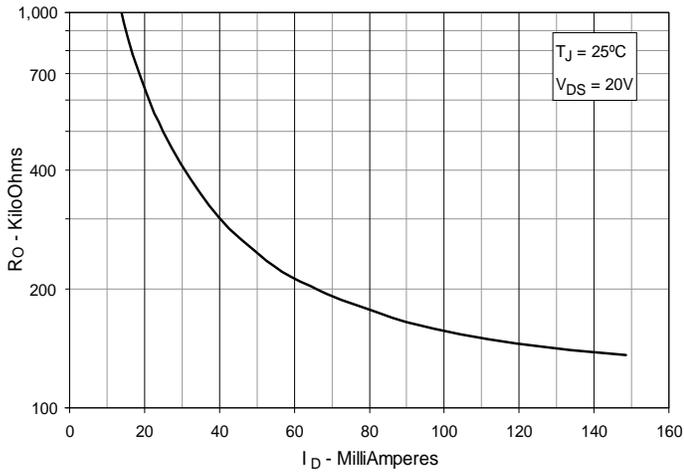


Fig. 8. Input Admittance

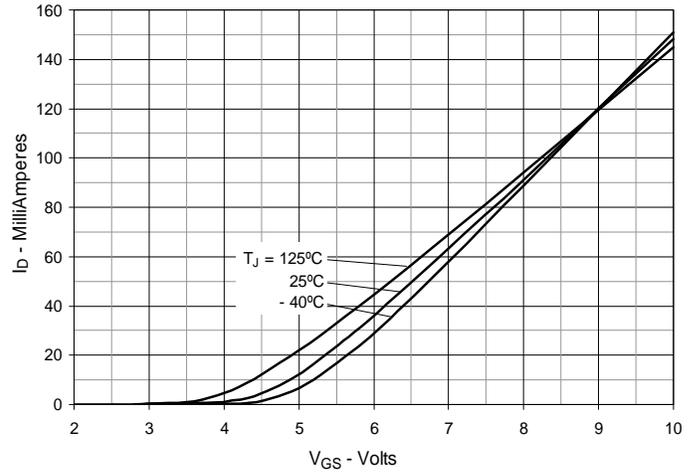


Fig. 9. Transconductance

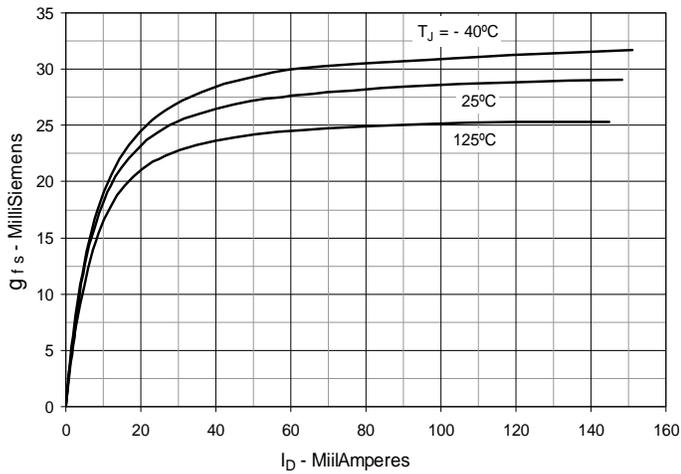


Fig. 10. Forward Voltage Drop of Intrinsic Diode

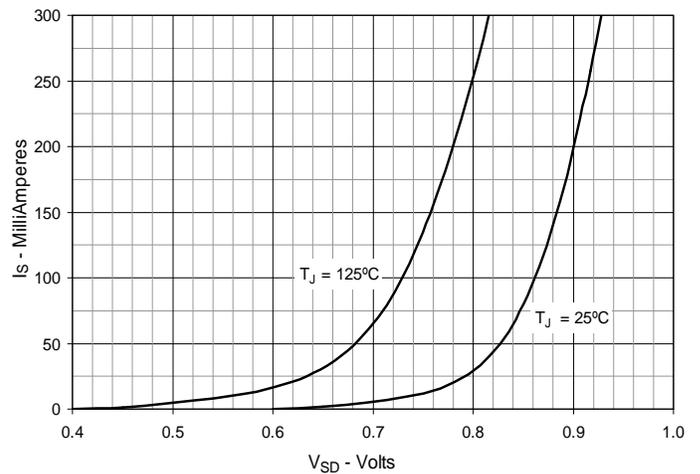


Fig. 11. Gate Charge

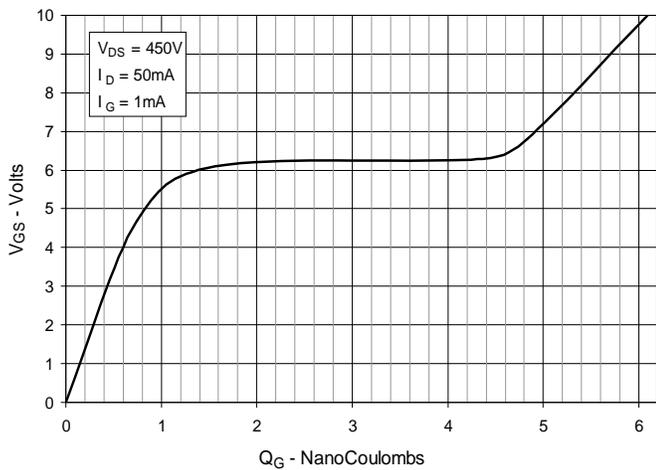


Fig. 12. Capacitance

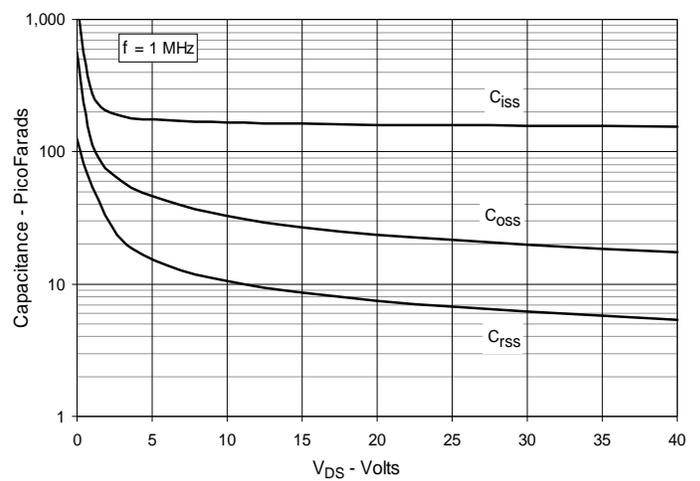


Fig. 13. Allowable Power Dissipation for Various Heat-Sinking Conditions

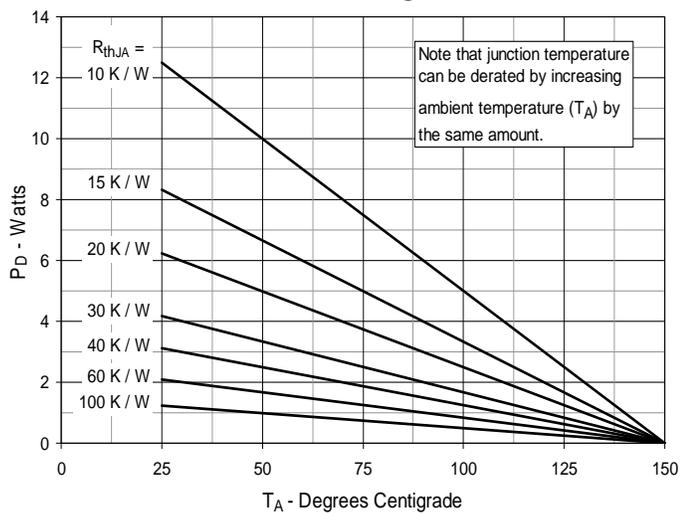


Fig. 14. Forward-Bias Safe Operating Area

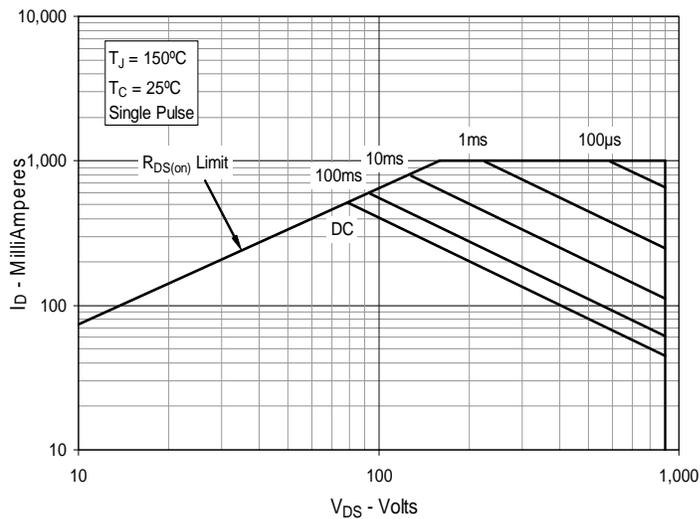


Fig. 15. Maximum Transient Thermal Impedance

